SQJ146EP

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Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.007
I _D (A)	75
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

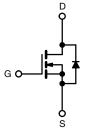
- TrenchFET[®] Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics



COMPLIANT HALOGEN

FREE

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T	_C = 25 °C, unles	s otherwise noted	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	40	v
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current	T _C = 25 °C ª	1	75	
Continuous drain current	T _C = 125 °C	۱ _D	43	
Continuous source current (diode conduction) ^a		I _S	62	A
Pulsed drain current ^b		I _{DM}	200	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	18.5	
Single pulse avalanche energy		E _{AS}	17	mJ
Maximum power dissipation ^b	T _C = 25 °C	PD	75	W
	$T_{\rm C} = 125 ^{\circ}{\rm C}$	25	vv	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d	, e		260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	70	°C/W
Junction-to-case (drain)		R _{thJC}	2	0/10

Notes

a. Package limited

b. Pulse test; pulse width \leq 300 $\mu s,\,duty\,cycle \leq$ 2 $\,\%$

c. When mounted on 1" square Pcb (Fr4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		40	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μΑ	2.5	3.0	3.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		V _{GS} = 0 V V _{DS} = 40 V		-	-	1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ³ 5 V	10	-	-	Α
		V _{GS} = 10 V	I _D = 15 A	-	0.0055	0.007	1
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 15 A, T _J = 125 °C	-	-	0.012	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.014	
Forward transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 5 A		-	25	-	S
Dynamic ^b		•		•			•
Input capacitance	C _{iss}			-	1072	1500	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	400	560	pF
Reverse transfer capacitance	C _{rss}			-	40	60	
Total gate charge ^c	Qg			-	18	27	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_D = 10 \text{ A}$	-	6	-	nC
Gate-drain charge ^c	Q _{gd}			-	5	-	1
Gate resistance	Rg	f = 1 MHz		2	4	6	Ω
Turn-on delay time ^c	t _{d(on)}			-	12	12	
Rise time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 20 \; V, \; R_{\text{L}} = 5 \; \Omega, \\ I_{\text{D}} \cong 4 \; A, \; V_{\text{GEN}} = 10 \; V, \; R_{\text{g}} = 1 \; \Omega \end{array}$		-	5	9	ns
Turn-off delay time ^c	t _{d(off)}			-	19	29	
Fall time ^c	t _f			-	5	9	
Source-Drain Diode Ratings and Charac	teristics ^b						
Pulsed current ^a	I _{SM}			-	-	200	Α
Forward voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V		-	-	1.1	V
Body diode reverse recovery time	t _{rr}			-	21	32	ns
Body diode reverse recovery charge	Q _{rr}	I _F = 10 A, di/dt = 100 A/μs		-	8	12	nC
Reverse recovery fall time	t _a			-	10	14	ns
Reverse recovery rise time	t _b			-	11	17	
Body diode peak reverse recovery current	I _{RM(REC)}			-	0.7	1.0	А

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

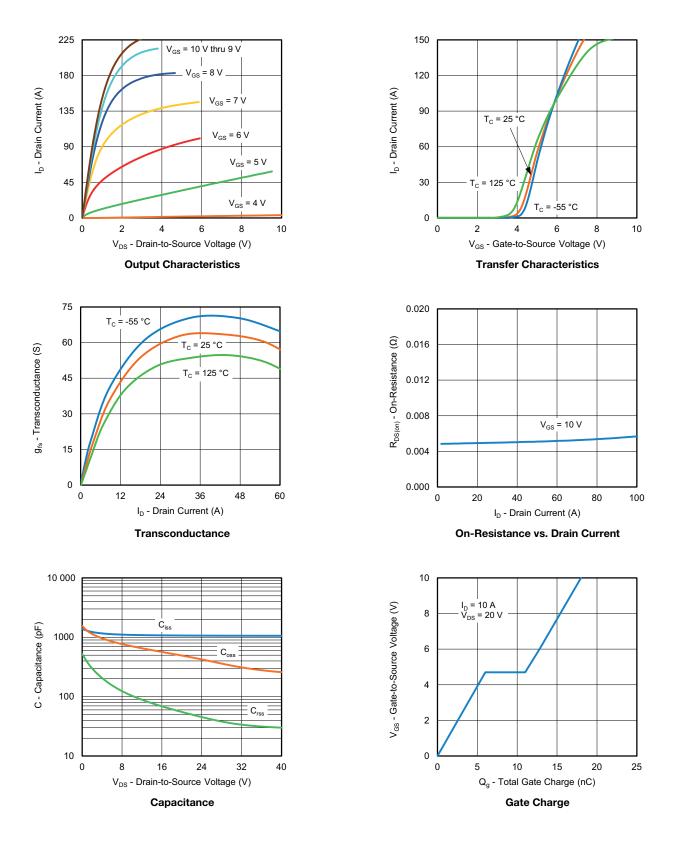
b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



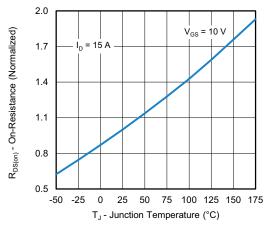
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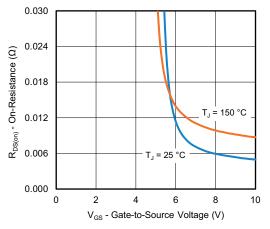
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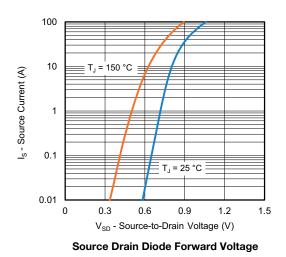
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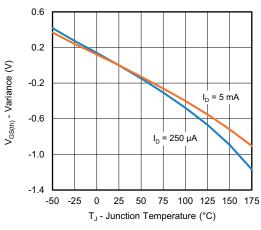


On-Resistance vs. Junction Temperature

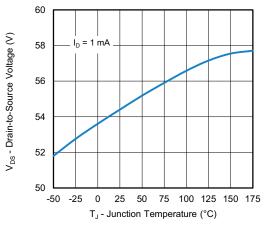


On-Resistance vs. Gate-to Source Voltage

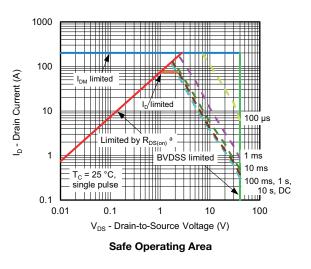




Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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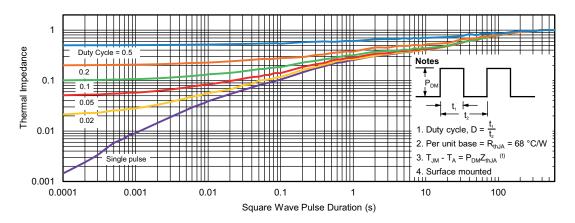
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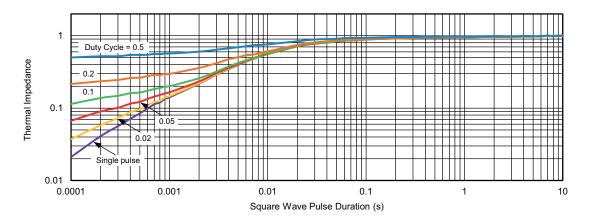
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

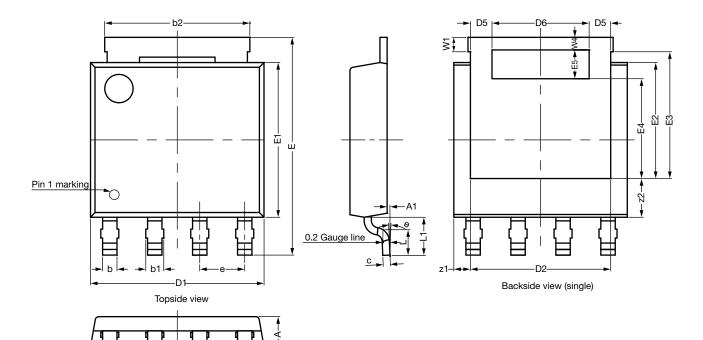
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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PowerPAK[®] SO-8L (PPKSO8LWLA) Case Outline 3



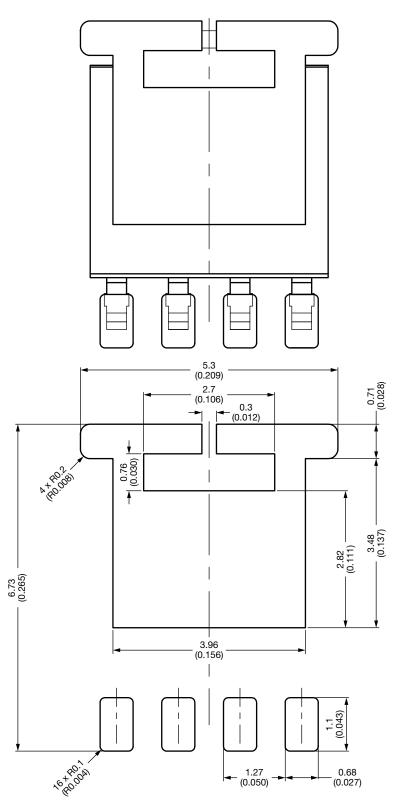
DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX	
А	1.00	1.05	1.10	0.039	0.041	0.043	
A1	0.00		0.127	0.000		0.005	
b	0.33	0.41	0.49	0.013	0.016	0.019	
b1	0.43	0.51	0.59	0.017	0.020	0.023	
b2	4.00	4.10	4.20	0.157	0.161	0.165	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D5	0.51	0.61	0.71	0.020	0.024	0.028	
D6	2.64	2.74	2.84	0.104	0.108	0.112	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
E3	3.48	3.58	3.68	0.137	0.141	0.145	
E4	2.72	2.82	2.92	0.107	0.111	0.115	
E5	0.71	0.81	0.91	0.028	0.032	0.036	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
W1	0.31	0.41	0.51	0.012	0.016	0.020	
W4	0.31	0.36	0.41	0.012	0.014	0.016	
z1	0.37	0.47	0.57	0.015	0.019	0.022	
z2	0.99	1.09	1.19	0.039	0.043	0.047	
θ	0°		5°	0°		5°	

Note

• Millimeter will govern



Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)

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